

Attorney's Docket No. 005819.P001

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Patent Application of:)

Jack Zezhong Peng)

Application No.: New Application)

Filed: Herewith)

For: SEMICONDUCTOR MEMORY)
CELL AND MEMORY ARRAY)
USING A BREAKDOWN PHENOMENA)
IN AN ULTRA-THIN DIELECTRIC)

Examiner: Not Yet Assigned

Art Unit: Not Yet Assigned



Commissioner for Patents
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

Sir:

Enclosed is a copy of Information Disclosure Citation Form PTO-1449 together with copies of the documents cited on that form. It is respectfully requested that the cited documents be considered and that the enclosed copy of Information Disclosure Citation Form PTO-1449 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

Pursuant to 37 C.F.R. § 1.97, the submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made and is not to be construed as an admission that the information cited in this statement is material to patentability.

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XXX 37 C.F.R. §1.97(b).

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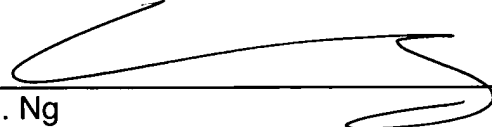
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If there are any additional charges, please charge Deposit Account No.
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Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Dated: 9/18, 2001


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PTO/SB/08A (10-96)

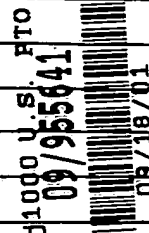
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				Application Number	New Application
				Filing Date	Herewith
				First Named Inventor	Jack Zezhong Peng
				Group Art Unit	Not yet assigned
Examiner Name	Not yet assigned				
Attorney Docket Number	005819.P001				
Sheet	1	of	1		



U.S. PATENT DOCUMENTS					
Examiner Initials *	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Filing Date if Appropriate
	Number				

FOREIGN PATENT DOCUMENTS						
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	✓ MIRANDA, ENRIQUE et al; Analytic Modeling of Leakage Current Through Multiple Breakdown Paths in SiO ₂ Films; 39th Annual International Reliability Physics Symposium; Orlando, FL 2001	
	✓ LOMBARDO, S. et al; Softening of Breakdown in Ultra-Thin Gate Oxide nMOSFET's at Low Inversion Layer Density; 39th Annual International Reliability Physics Symposium; Orlando, FL 2001	
	✓ WU, E.W. et al; Voltage-Dependent Voltage-Acceleration of Oxide Breakdown for Ultra-Thin Oxides; IEEE, 2000.	
	✓ RASRAS, MAHMOUD et al; Substrate Hole Current Origin After Oxide Breakdown; IEEE, 2000.	
	SUNE, JORDI et al.; Post Soft Breakdown Conduction in SiO ₂ Gate Oxides; IEEE, 2000.	

Examiner Signature	Date Considered
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